

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE40P25G uses uses advanced trench technology to provide excellent $R_{\text{DS(ON)}}$, This device is suitable for use as a load switch or power management.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

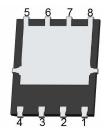
100% UIS TESTED! 100% ΔVds TESTED!

General Features

- V_{DS} =-40V, I_D =-25A $R_{DS(ON)}$ =11.5mΩ (typical) @ V_{GS} =10V $R_{DS(ON)}$ =18.5mΩ (typical) @ V_{GS} =4.5V
- High density cell design for ultra low Rdson
- Very low on-resistance R_{DS(on)}
- Good stability and uniformity with high E_{AS}
- 150 °C operating temperature
- Pb-free lead plating

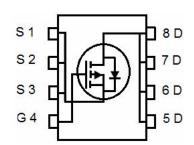
DFN 5X6





Top View

Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40P25G	NCE40P25G	DFN 5x6-8L	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	-25	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-100	Α
Maximum Power Dissipation	P _D	35	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	R _{eJC}	3.6	°C/W



Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-40V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	lgss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.2	-1.8	-2.4	V
Dunin Course On Otata Basistana	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	11.5	14	0
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	18.5	23	mΩ
Forward Transconductance	g FS	V _{DS} =-10V,I _D =-20A	-	25	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}	V _{DS} =-20V,V _{GS} =0V, F=1.0MHz	-	2960	-	PF
Output Capacitance	C _{oss}		-	370	-	PF
Reverse Transfer Capacitance	C _{rss}	T-1.UIVITZ	-	310	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	t _r	V _{DD} =-20V, ID=-20A,	-	18	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_{GEN} =3 Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	24	-	nS
Total Gate Charge	Qg		-	42.2	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-20V,I _D =-20A,V _{GS} =-10V	-	6.9	-	nC
Gate-Drain Charge	Q_{gd}		-	9.7	-	nC
Drain-Source Diode Characteristics	Drain-Source Diode Characteristics					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-20A	-	-	-1.2	V

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

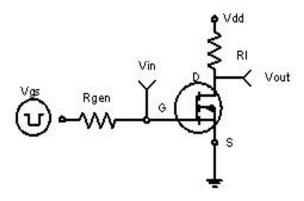


Figure 1 Switching Test Circuit

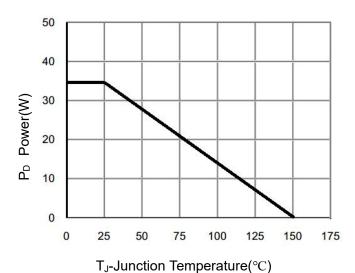


Figure 3 Power Dissipation

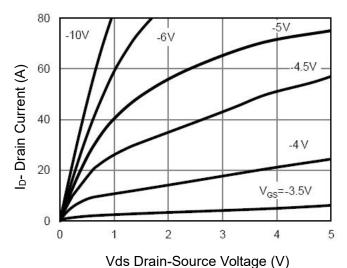


Figure 5 Output Characteristics

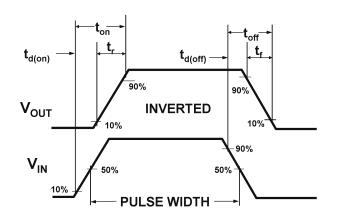
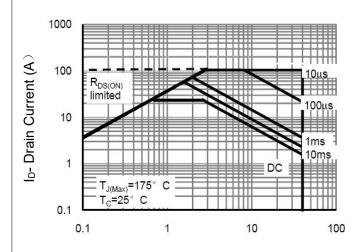


Figure 2 Switching Waveforms



Vds Drain-Source Voltage (V)
Figure 4 Safe Operation Area

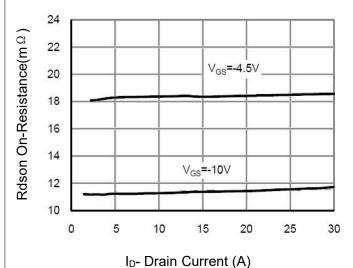
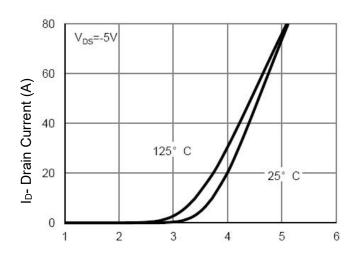


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)



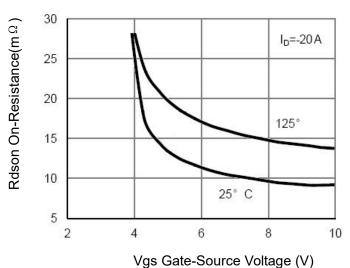


Figure 9 Rdson vs Vgs

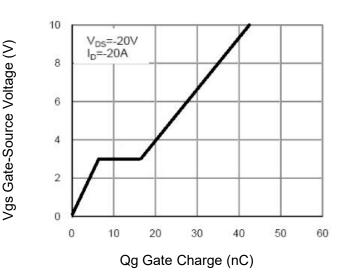


Figure 11 Gate Charge

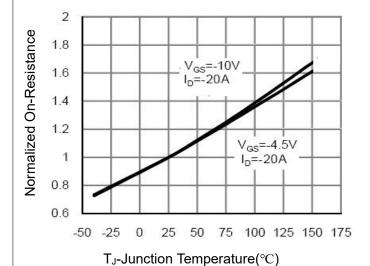


Figure 8 Drain-Source On-Resistance

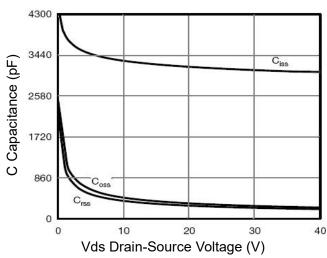


Figure 10 Capacitance vs Vds

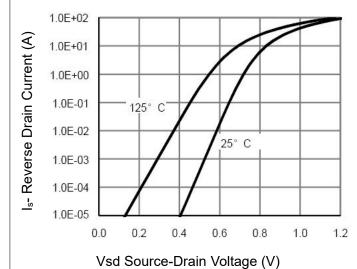


Figure 12 Source- Drain Diode Forward



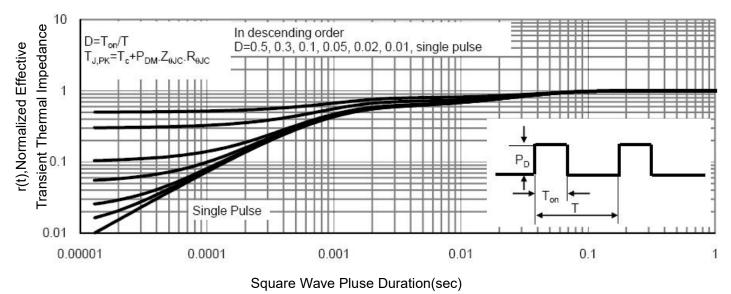
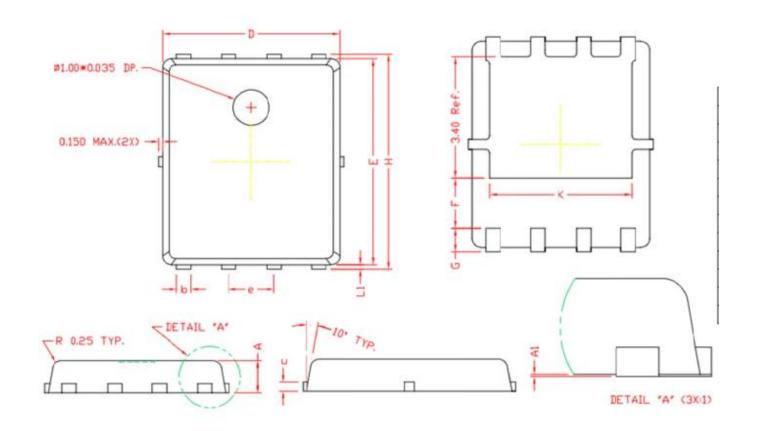


Figure 13 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX		
A	0.80	0.90	1.00		
A1	0.00	0.03	0.05		
b	0.35	0.42			
С	0.	. 254 REF	?.		
D	4.90	5.00	5.10		
F	1	. 40 REF			
E	5.70	5. 80	5. 90		
е	1.27 BSC.				
Н	5. 95	6.08	6. 20		
L1	0.10	0. 14	0.18		
G	0	. 60 REF			
K	4	. 00 REF			

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